

2N2905A

Small Signal Switching Transistor

PNP Silicon

Features

- MIL-PRF-19500/290 Qualified
- Available as JAN, JANTX, and JANTXV

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V_{CEO}	–60	Vdc
Collector – Base Voltage	V_{CBO}	–60	Vdc
Emitter – Base Voltage	V_{EBO}	–5.0	Vdc
Collector Current – Continuous	I_C	–600	mA _{dc}
Total Device Dissipation @ $T_A = 25^\circ\text{C}$	P_T	800	mW
Total Device Dissipation @ $T_C = 25^\circ\text{C}$	P_T	3.0	W
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–65 to +200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

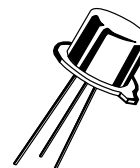
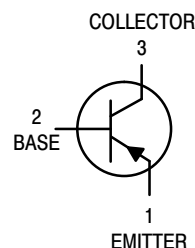
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	195	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	50	$^\circ\text{C/W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



ON Semiconductor®

<http://onsemi.com>



TO-39
CASE 205AB
STYLE 1

ORDERING INFORMATION

Device	Package	Shipping
JAN2N2905A	TO-39	Bulk
JANTX2N2905A		
JANTXV2N2905A		

2N2905A

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (Note 1) ($I_C = -10\text{ mAdc}$)	$V_{(BR)CEO}$	-60	–	Vdc
Collector–Emitter Cutoff Current ($V_{CE} = -60\text{ Vdc}$)	I_{CES}	–	-1.0	μAdc
Collector–Base Cutoff Current ($V_{CB} = -50\text{ Vdc}$) ($V_{CB} = -60\text{ Vdc}$)	I_{CBO}	– –	-10 -10	nAdc μAdc
Emitter–Base Cutoff Current ($V_{EB} = -5.0\text{ Vdc}$) ($V_{EB} = -3.5\text{ Vdc}$)	I_{EBO}	– –	-10 -50	μAdc nAdc
ON CHARACTERISTICS (Note 1)				
DC Current Gain ($I_C = -0.1\text{ mAdc}$, $V_{CE} = -10\text{ Vdc}$) ($I_C = -1.0\text{ mAdc}$, $V_{CE} = -10\text{ Vdc}$) ($I_C = -10\text{ mAdc}$, $V_{CE} = -10\text{ Vdc}$) ($I_C = -150\text{ mAdc}$, $V_{CE} = -10\text{ Vdc}$) ($I_C = -500\text{ mAdc}$, $V_{CE} = -10\text{ Vdc}$)	h_{FE}	75 100 100 100 50	– 450 – 300 –	–
Collector–Emitter Saturation Voltage ($I_C = -150\text{ mAdc}$, $I_B = -15\text{ mAdc}$) ($I_C = -500\text{ mAdc}$, $I_B = -50\text{ mAdc}$)	$V_{CE(sat)}$	– –	-0.4 -1.6	Vdc
Base–Emitter Saturation Voltage ($I_C = -150\text{ mAdc}$, $I_B = -15\text{ mAdc}$) ($I_C = -500\text{ mAdc}$, $I_B = -50\text{ mAdc}$)	$V_{BE(sat)}$	– –	-1.3 -2.6	Vdc
SMALL–SIGNAL CHARACTERISTICS				
Magnitude of Small Signal Current Gain ($I_C = -50\text{ mAdc}$, $V_{CE} = -20\text{ Vdc}$, $f = 100\text{ MHz}$)	$ h_{fe} $	2.0	–	–
Small Signal Current Gain ($I_C = -1.0\text{ mAdc}$, $V_{CE} = -10\text{ Vdc}$, $f = 1\text{ kHz}$)	h_{fe}	100	–	–
Output Capacitance ($V_{CB} = -10\text{ Vdc}$, $I_E = 0$, $100\text{ kHz} \leq f \leq 1.0\text{ MHz}$)	C_{obo}	–	8.0	pF
Input Capacitance ($V_{EB} = -2.0\text{ Vdc}$, $I_C = 0$, $100\text{ kHz} \leq f \leq 1.0\text{ MHz}$)	C_{ibo}	–	30	pF
SWITCHING CHARACTERISTICS				
Turn–On Time (Reference Figure in MIL–PRF–19500/290)	t_{on}	–	45	ns
Turn–Off Time (Reference Figure in MIL–PRF–19500/290)	t_{off}	–	300	ns

1. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

